

## CLAIMS

Claim 1. (Cancelled).

Claim 2. (Presently amended) The method according to ~~Claim 1~~ Claim 3 wherein said optoelectronic device epitaxial wafer includes an  $\text{Al}_2\text{O}_3$  substrate, a n-GaN (Gallium-Nitride) layer, a MQW (Multi-Quantum-Well) layer, a p-AlGaN layer and a p-GaN layer.

Claim 3. (Presently amended) A method for manufacturing a compound semiconductor optoelectronic device comprising steps of:

forming an optoelectronic device epitaxial wafer,  
said optoelectronic device epitaxial wafer containing  
a V-shaped pit due to threading dislocation;  
forming an insulated isolation material in said V-  
shaped pit of said optoelectronic device epitaxial  
wafer; and  
forming an electrode layer on said optoelectronic  
device epitaxial wafer having said insulated isolation  
material in said V-shaped pit for completing said  
optoelectronic device, ~~The method according to Claim 1~~  
wherein forming said insulated isolation material  
comprises steps of:

forming said insulated isolation material layer on  
said V-shaped surface; and

removing said insulated isolation material layer but  
leaving said insulated isolation material in said V-  
shaped pit.

Claim 4. (Original) The method according to Claim 3 wherein

forming said insulated isolation material layer is by deposition.

Claim 5. (Original) The method according to Claim 4 wherein removing said insulated isolation material layer is by polishing.

Claim 6. (Original) The method according to Claim 4 wherein removing said insulated isolation material layer is by etching.

Claim 7. (Original) The method according to Claim 4 wherein removing said insulated isolation material layer is by reactive ion etching and said optoelectronic epitaxial wafer is inclined.

Claim 8. (Original) The method according to Claim 3 wherein forming said insulated isolation material layer is by coating an organic material.

Claims 9-15. Cancelled.